



EXPRESS MAIL NO. EL897863842US

PATENT

#8/c
up
1/16/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Robert Louis Hodges
Application No. : 09/733,243 ✓
Filed : December 7, 2000
For : SELF-ALIGNED GATE AND METHOD

Examiner : Michael Manh Trinh
Art Unit : 2822
Docket No. : 98-P-104C1 (850063.542C1)
Date : January 3, 2003

RECEIVED
JAN - 8 2003
TECHNOLOGY CENTER 2800

Commissioner for Patents
Washington, DC 20231

AMENDMENT

Commissioner for Patents:

In response to the Office Action dated July 3, 2002, please extend the period of time for response three (3) months, to expire on January 3, 2003. Enclosed are a Petition for an Extension of Time and the requisite fee. Please amend the application as follows:

In the Specification:

Please replace the paragraph beginning at line 16, page 5, with the following rewritten paragraph:

C1
In a step 46, a second layer 48 is formed on the first layer 44. The second layer 48 is formed from a material that is chemically different than the first layer 44. As a result, the second layer 48 may be etched by an etching process that does not etch the first layer 44. The shallow trench isolation structures 39 are protected from etching processes that could damage or affect them by chemical selectivity with respect to the second layer 48, *i.e.*, etching processes for